

# 2SD768(K)

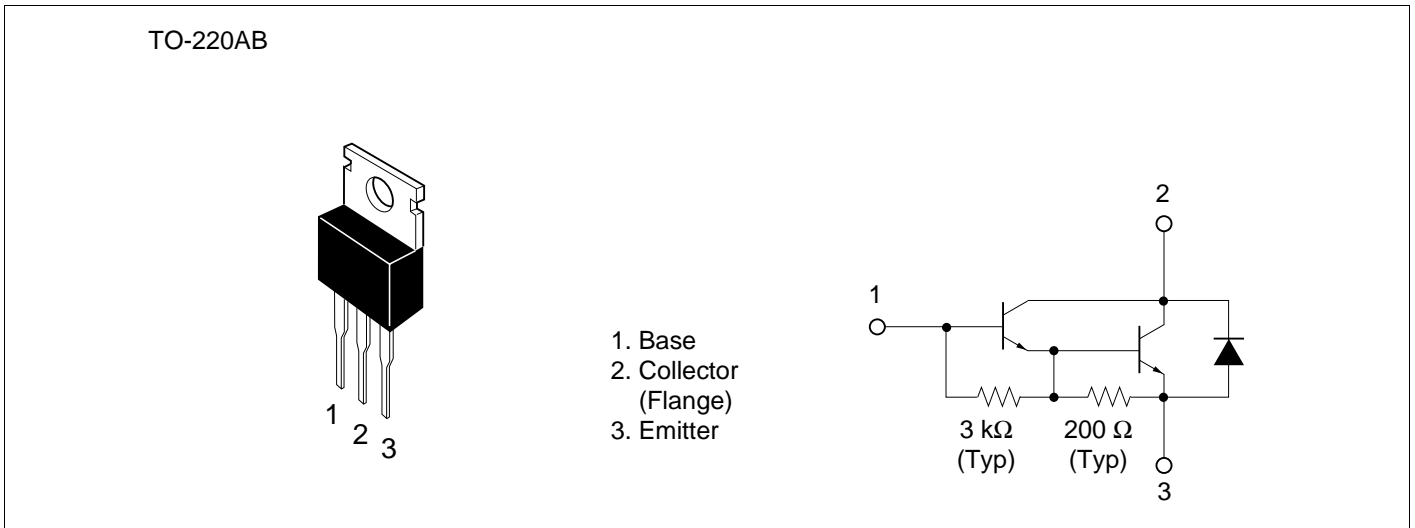
Silicon NPN Epitaxial

# HITACHI

## Application

Medium speed and power switching complementary pair with 2SB727(K)

## Outline



## Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	120	V
Collector to emitter voltage	$V_{CEO}$	120	V
Emitter to base voltage	$V_{EBO}$	7	V
Collector current	$I_C$	6	A
Collector peak current	$I_{C(peak)}$	10	A
Collector power dissipation	$P_C^{*1}$	40	W
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

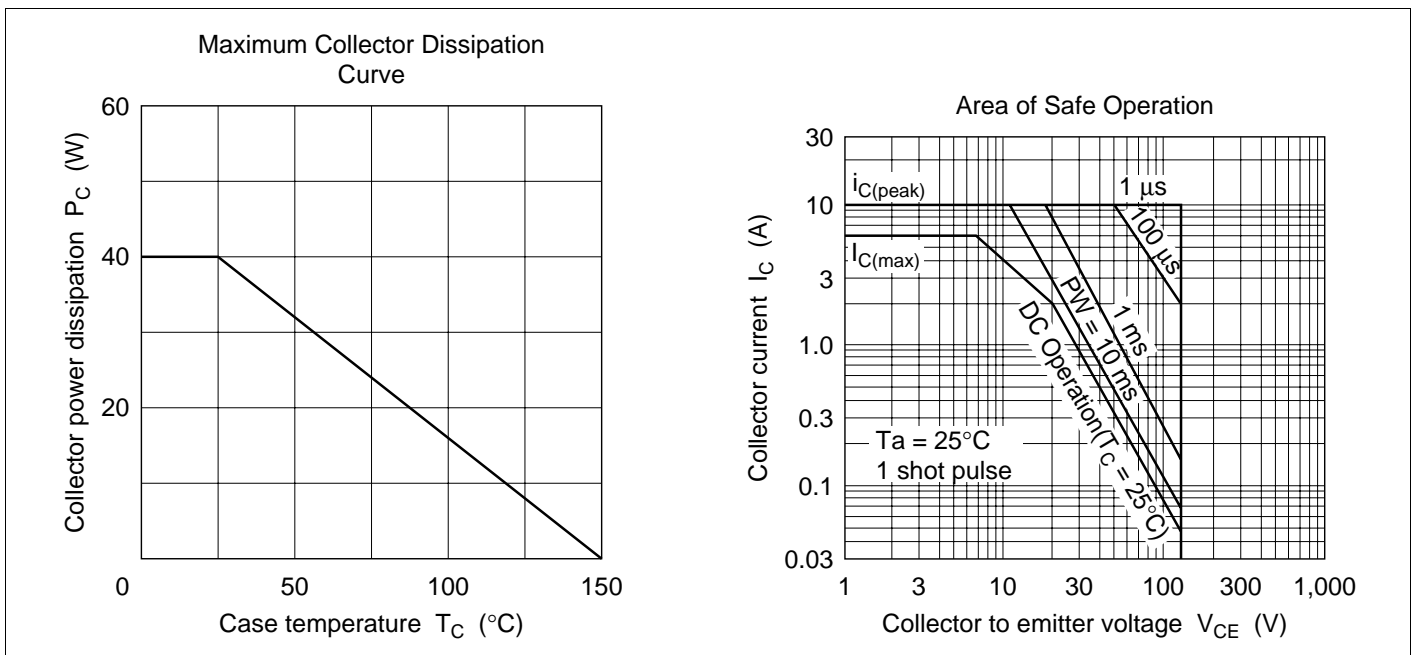
Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

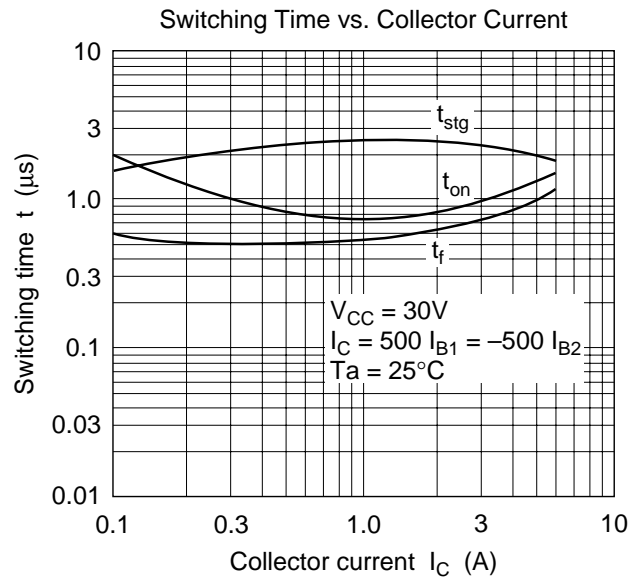
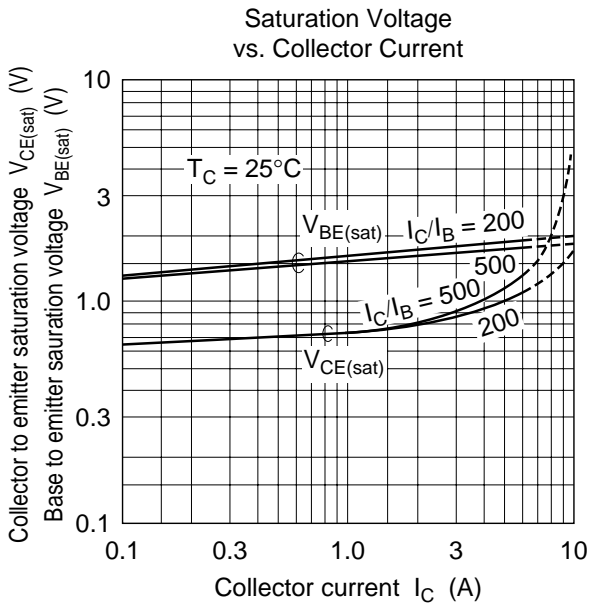
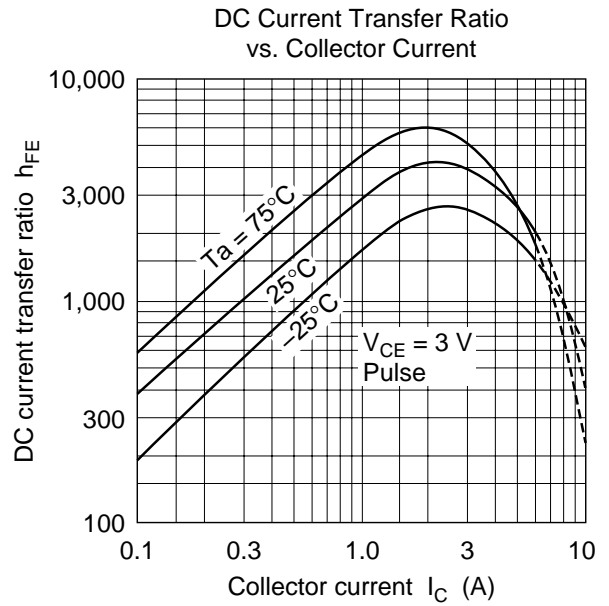
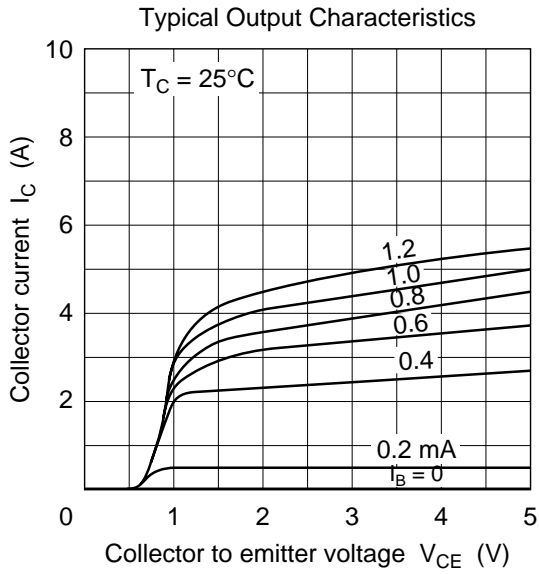
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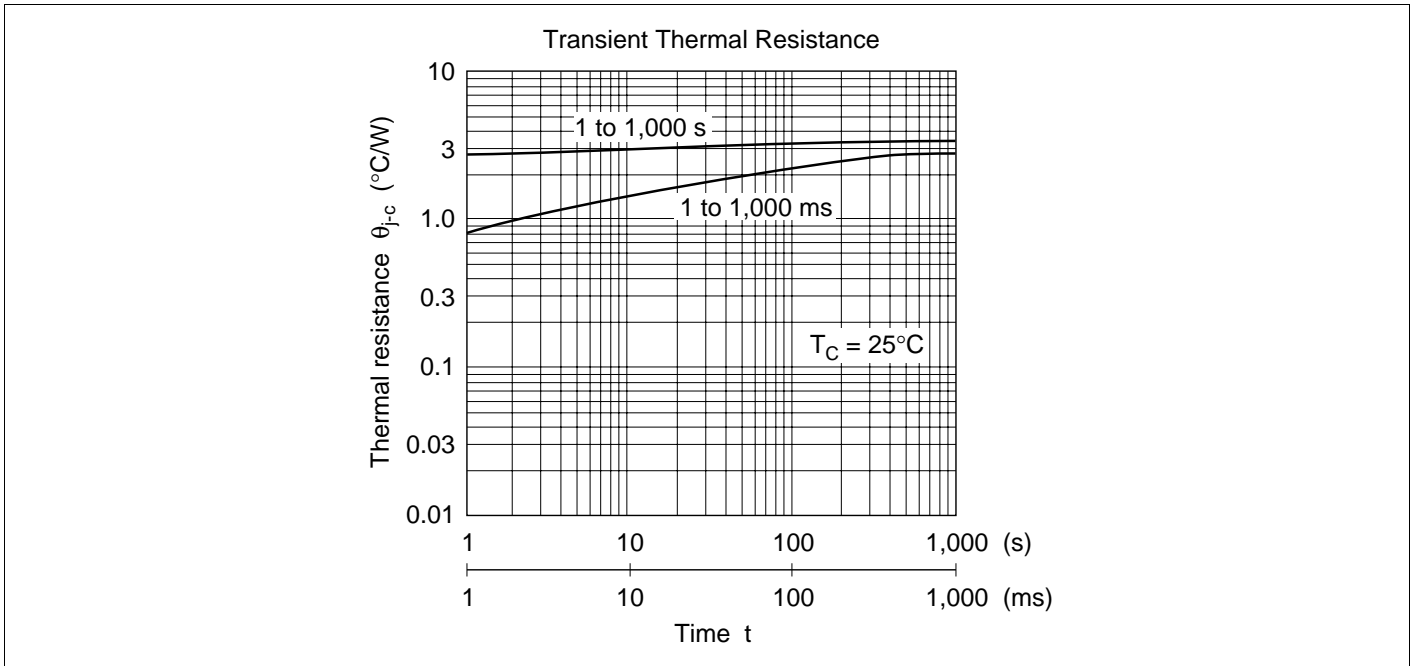
## Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	V	$I_C = 25 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	7	—	—	V	$I_E = 50 \text{ mA}, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	100	$\mu\text{A}$	$V_{CB} = 120 \text{ V}, I_E = 0$
	$I_{CEO}$	—	—	10	$\mu\text{A}$	$V_{CE} = 100 \text{ V}, R_{BE} = \infty$
DC current transfer ratio	$h_{FE}$	1000	—	20000		$V_{CE} = 3 \text{ V}, I_C = 3 \text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	—	1.5	V	$I_C = 3 \text{ A}, I_B = 6 \text{ mA}^{*1}$
	$V_{CE(sat)2}$	—	—	3	V	$I_C = 6 \text{ A}, I_B = 60 \text{ mA}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)1}$	—	—	2	V	$I_C = 3 \text{ A}, I_B = 6 \text{ mA}^{*1}$
	$V_{BE(sat)2}$	—	—	3.5	V	$I_C = 6 \text{ A}, I_B = 60 \text{ mA}^{*1}$
Turn on time	$t_{on}$	—	1.0	—	$\mu\text{s}$	$I_C = 3 \text{ A}, I_{B1} = -I_{B2} = 6 \text{ mA}$
Turn off time	$t_{off}$	—	3.0	—	$\mu\text{s}$	$I_C = 3 \text{ A}, I_{B1} = -I_{B2} = 6 \text{ mA}$

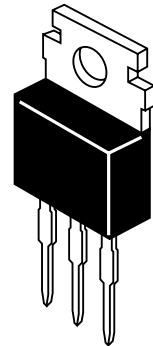
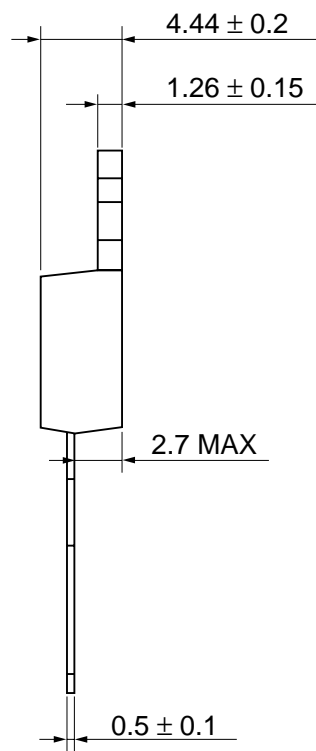
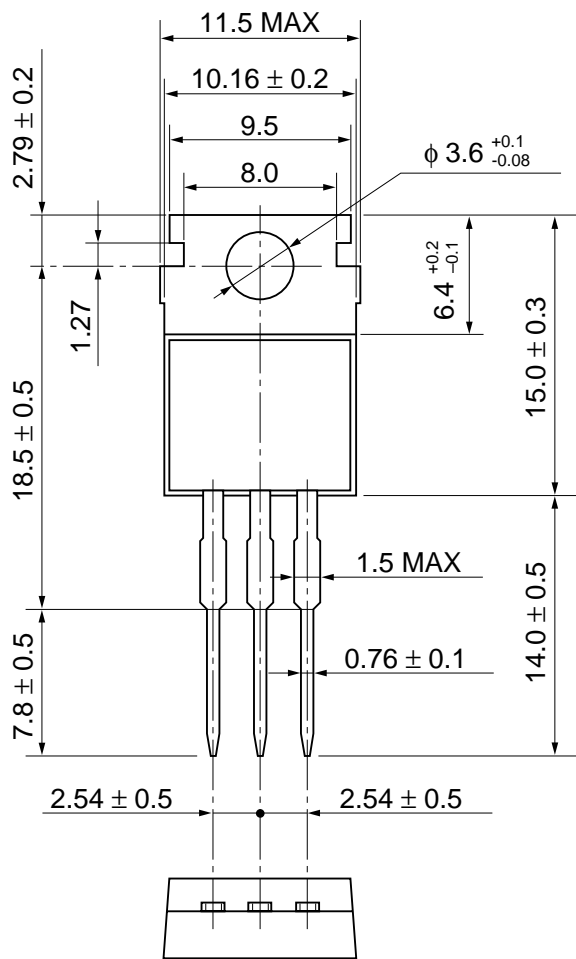
Note: 1. Pulse test.







Unit: mm



Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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